FAIRCHILD SEMICONDUCTOR

FDC602P

P-Channel 2.5V Specified PowerTrench[®] MOSFET

General Description

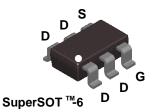
This P-Channel 2.5V specified MOSFET uses a rugged gate version of Fairchild's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V - 12V).

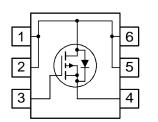
Applications

- Battery management
- Load switch
- Battery protection

Features

- -5.5 A, -12 V $R_{DS(ON)} = 0.033 \ \Omega \ @ V_{GS} = -4.5 \ V$ $R_{DS(ON)} = 0.052 \ \Omega \ @ V_{GS} = -2.5 \ V$
- Fast switching speed.
- High performance trench technology for extremely low $R_{\text{DS}(\text{ON})}$.





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-12	V
V _{GSS}	Gate-Source Voltage		±12	V
ID	Drain Current – Continuous	(Note 1a)	-5.5	A
	- Pulsed		-30	
PD	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C
Therma	I Characteristics			
R _{0JA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R _{0JC}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.602	FDC602P	7"	8mm	3000 units

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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_D = -250 \mu A$	-12			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
I _{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 12 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12 V$ $V_{DS} = 0 V$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	-0.6		-1.5	V
$R_{\text{DS(on)}}$	Static Drain–Source On–Resistance	$ \begin{array}{ll} V_{GS} = -4.5 \ V, & I_{D} = -5.5 \ A \\ V_{GS} = -2.5 \ V, & I_{D} = -4.4 \ A \end{array} $			0.033 0.052	Ω
Drain-S	ource Diode Characteristics	and Maximum Ratings	•	•	•	
ls	Maximum Continuous Drain–Source Diode Forward Current –1.3 A					
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V$, $I_{S} = -1.3 A$ (Note 2)			-1.2	V

Notes:

1. R_{BJA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

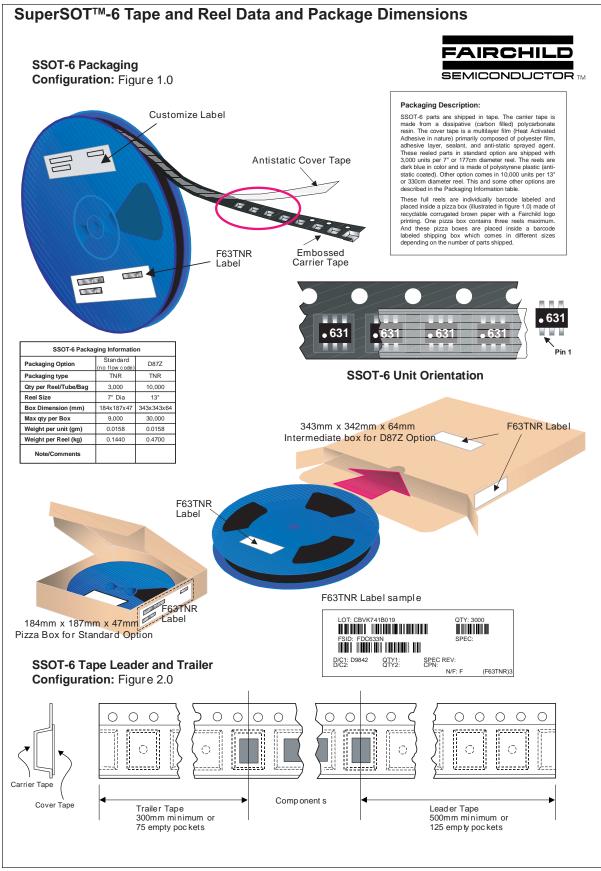
a. $~78^\circ C/W$ when mounted on a $1 in^2\, pad$ of 2oz copper on FR-4 board.

b. 156°C/W when mounted on a minimum pad.

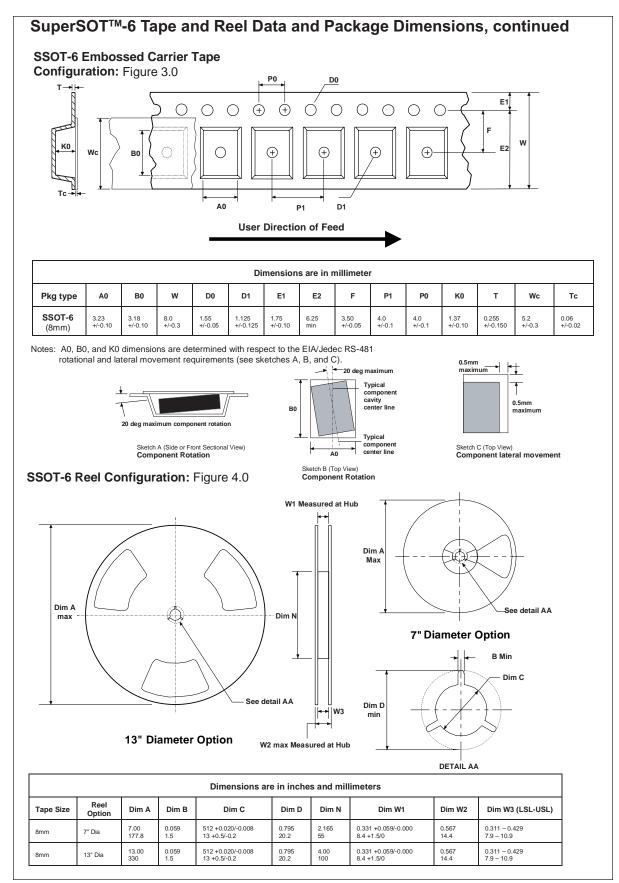
2. Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%

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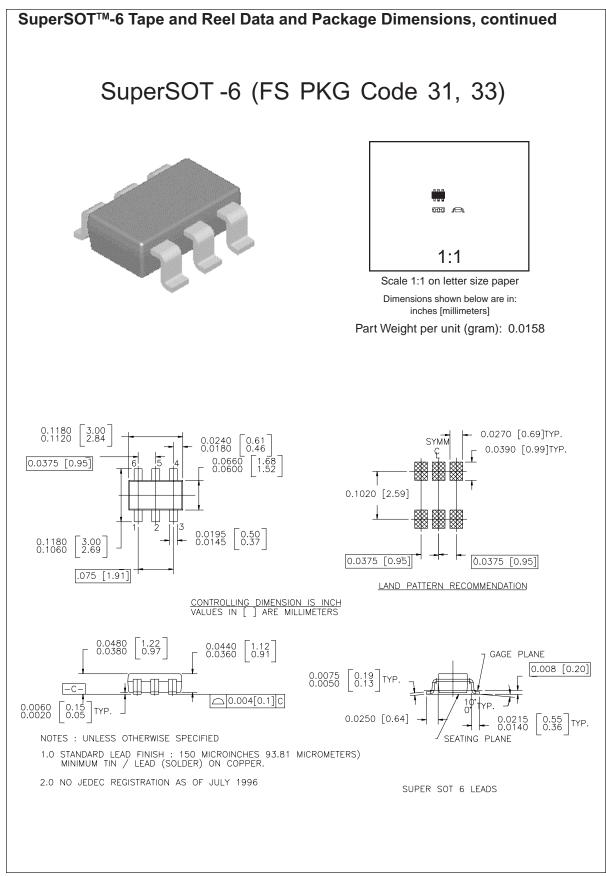
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August 1999, Rev. C







September 1998, Rev. A

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